

2SD1419

Silicon NPN Epitaxial

REJ03G0788-0200 (Previous ADE-208-1150) Rev.2.00 Aug.10.2005

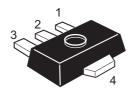
Application

- Low frequency power amplifier
- Complementary pair with 2SB1026

Outline

RENESAS Package code: PLZZ0004CA-A

(Package name: UPAK®)



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)

Note: Marking is "DE".

*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|------------------------------|-------------------------------|-------------|------|
| Collector to base voltage | V _{CBO} | 120 | V |
| Collector to emitter voltage | V _{CEO} | 100 | V |
| Emitter to base voltage | V _{EBO} | 5 | V |
| Collector current | I _C | 1 | A |
| Collector peak current | i _{C(peak)} *1 | 2 | A |
| Collector power dissipation | P _C * ² | 1 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

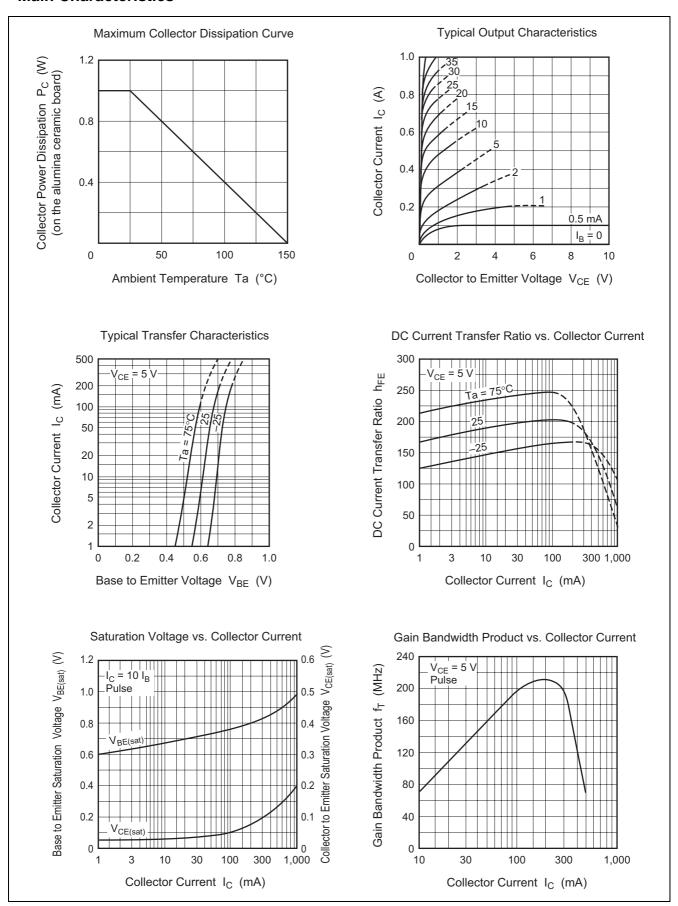
Electrical Characteristics

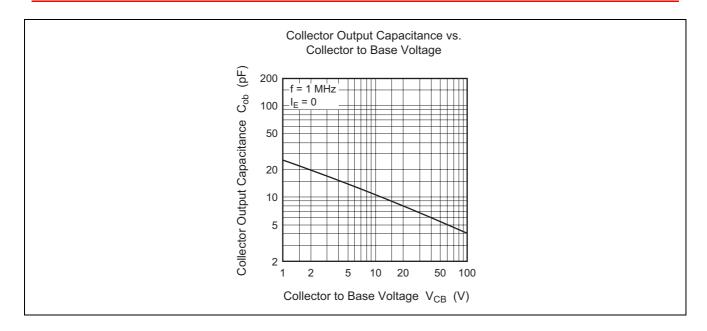
 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|------------------|-----|-----|-----|------|---|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 120 | _ | _ | V | $I_C = 10 \mu A, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 100 | _ | _ | V | I_C = 1 mA, R_{BE} = ∞ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 5 | _ | _ | V | $I_E = 10 \mu A, I_C = 0$ |
| Collector cutoff current | I _{CBO} | | _ | 10 | μΑ | $V_{CB} = 100 \text{ V}, I_E = 0$ |
| DC current transfer ratio | h _{FE1} | 100 | _ | 200 | | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA*}^{1}$ |
| | h _{FE2} | 30 | _ | _ | | $V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA*}^{1}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | | _ | 1 | V | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}*^1$ |
| Base to emitter voltage | V_{BE} | _ | _ | 1.5 | V | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA*}^{1}$ |
| Gain bandwidth product | f⊤ | | 140 | _ | MHz | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA*}^{1}$ |
| Collector output capacitance | Cob | _ | 12 | _ | pF | $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ |

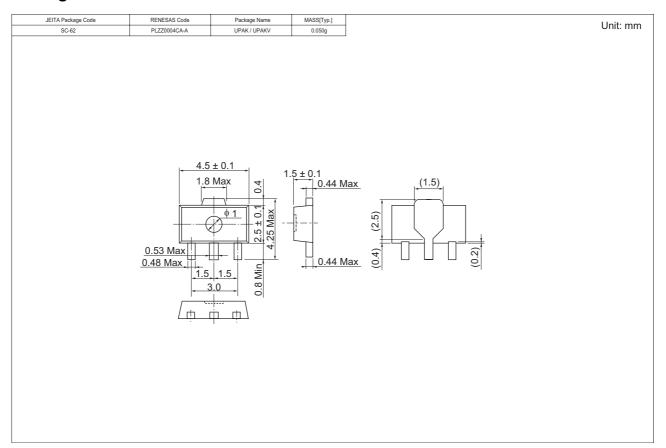
Notes: 1. Pulse test

Main Characteristics





Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|---------------|----------|------------------------------------|
| 2SD1419DETL-E | 1000 | φ 178 mm Reel, 12 mm Emboss Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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